

February, 2009

FPDB40PH60B

Smart Power Module for Front-End Rectifier

General Description

FPDB40PH60B is an advanced smart power module of PFC(Power Factor Correction) that Fairchild has newly developed and designed mainly targeting mid-power application especially for an air conditioners. It combines optimized circuit protection and drive IC matched to high frequency switching IGBTs. System reliability is futher enhanced by the integrated under-voltage lock-out and over-current protection function.

Features

- Low thermal resistance due to Al₂O₃-DBC substrate
- 600V-40A 2-phase IGBT PWM semi-converter including a drive IC for gate driving and protection
- Typical switching frequency of 20kHz
- Isolation rating of 2500Vrms/min.

Applications

• AC 180V ~ 264V single-phase front-end rectifier

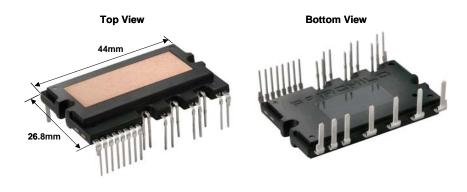


Fig. 1.

Integrated Power Functions

• PFC converter for single-phase AC/DC power conversion (Please refer to Fig. 3)

Integrated Drive, Protection and System Control Functions

- For IGBTs: Gate drive circuit, Overcurrent circuit protection (OC), Control supply circuit under-voltage (UV) protection
- Fault signaling: Corresponding to a UV fault
- Input interface: 5V CMOS/LSTTL compatible, Schmitt trigger input

Pin Configuration

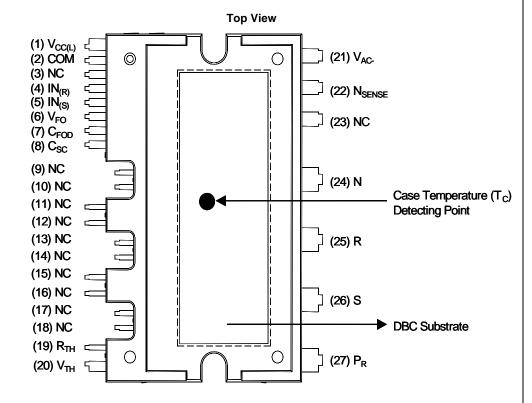


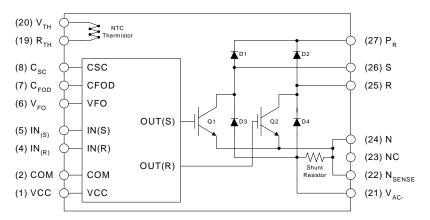
Fig. 2.

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Pin Descriptions

Pin Number	Pin Name	Pin Description
1	V _{CC}	Common Bias Voltage for IC and IGBTs Driving
2	COM	Common Supply Ground
4	IN _(R)	Signal Input for Low-side R-phase IGBT
5	IN _(S)	Signal Input for Low-side S-phase IGBT
6	V _{FO}	Fault Output
7	C _{FOD}	Capacitor for Fault Output Duration Time Selection
8	C _{SC}	Capacitor (Low-pass Filter) for Over Current Detection
19	R _(TH)	NTC Thermistor terminal
20	V _(TH)	NTC Thermistor terminal
21	V _{AC-}	Current Sensing Terminal
22	N _{SENSE}	Current Sensing Reference Terminal
24	N	Negative Rail of DC-Link
25	R	Output for R Phase
26	S	Output for S Phase
27	P_{R}	Positive Rail of DC-Link
3, 9~18, 23	NC	No Connection

Internal Equivalent Circuit and Input/Output Pins



Note:
1) Converter is composed of two IGBTs including four diodes and one IC which has gate driving and protection functions.

Fig. 3.

Absolute Maximum Ratings (T_J = 25°C, Unless Otherwise Specified)

Converter Part

Item	Symbol	Condition	Rating	Unit
Supply Voltage	V _i	Applied between R-S	264	V_{RMS}
Supply Voltage (Surge)	V _{i(Surge)}	Applied between R-S	500	V
Output Voltage	V_{PN}	Applied between P- N	450	V
Output Voltage (Surge)	V _{PN(Surge)}	Applied between P- N	500	V
Collector-emitter Voltage	V _{CES}		600	V
Each IGBT collector current	± I _C	T _C = 25°C	40	Α
Each IGBT collector current (Peak)	± I _{CP}	T _C = 25°C, Under 1ms pulse width	70	Α
Collector Dissipation	P _C	T _C = 25°C per One IGBT	113	W
Repetitive Peak Reverse Voltage	V_{RRM}		600	V
Peak Forward Surge Current	I _{FSM}	Single half sine-wave	350	Α
Power Rating of Shunt Resistor	P _{RSH}	T _C < 125°C	2	W
Operating Junction Temperature	TJ	(Note 1)	-40 ~ 150	°C

Control Part

Item	Symbol	Condition	Rating	Unit
Control Supply Voltage	V _{CC}	Applied between V _{CC} - COM	20	V
Input Signal Voltage	V _{IN}	Applied between IN - COM	-0.3~17	V
Fault Output Supply Voltage	V_{FO}	Applied between V _{FO} - COM	-0.3~V _{CC} +0.3	V
Fault Output Current	I _{FO}	Sink Current at V _{FO} Pin	5	mA
Current Sensing Input Voltage	V _{SC}	Applied between C _{SC} - COM	-0.3~V _{CC} +0.3	V

Total System

Item	Symbol	Condition	Rating	Unit
Module Case Operation Temperature	T _C		-20 ~ 100	°C
Storage Temperature	T _{STG}		-40 ~ 150	°C
Isolation Voltage	V _{ISO}	60Hz, Sinusoidal, AC 1 minute, Connection Pins to DBC	2500	V _{rms}

Thermal Resistance

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Junction to Case Thermal	$R_{\theta(j-c)Q}$	IGBT	-	-	1.1	°C/W
Resistance	$R_{\theta(j-c)HD}$	High-side diode	-	-	1.9	°C/W
(Referenced to PKG center)	$R_{\theta(j-c)LD}$	Low-side diode	-	-	1.4	°C/W

Note:

2. For the measurement point of case temperature($T_{\mbox{\scriptsize C}}$), please refer to Fig. 2.

Note: 1. The maximum junction temperature rating of the power chips integrated within the SPM is $150^{\circ}\text{C}(@T_{C} \le 100^{\circ}\text{C})$. However, to insure safe operation of the SPM, the average junction temperature should be limited to $T_{J(ave)} \le 125^{\circ}\text{C}$ ($@T_{C} \le 100^{\circ}\text{C}$).

$\textbf{Electrical Characteristics} \ \, (T_J = 25^{\circ}\text{C}, \, \text{Unless Otherwise Specified})$

Converter Part

ltem	Symbol	Condition	Min.	Тур.	Max.	Unit
IGBT saturation voltage	V _{CE(sat)}	$V_{CC} = 15V, V_{IN} = 5V; I_{C} = 40A$	-	1.8	2.3	V
High-side diode voltage	V _{FH}	I _F = 40A	-	2.2	2.7	V
Low-side diode voltage	V_{FL}	I _F = 40A	-	1.15	1.55	V
Switching Times	t _{ON}	$V_{PN} = 400V, V_{CC} = 15V, I_{C} = 40A$	-	500	-	ns
	t _{C(ON)}	V _{IN} = 0V ↔ 5V, Inductive Load	-	180	-	ns
	t _{OFF}	(Note 3)	-	500	-	ns
	t _{C(OFF)}	((1010-0)	-	90	-	ns
	t _{rr}		-	43	-	ns
	I _{rr}		-	6	-	Α
Current sensing resistor	R _{SENSE}		1.8	2.0	2.2	mΩ
Collector - emitter Leakage Current	I _{CES}	$V_{CE} = V_{CES}$	-	-	250	μА

Control Part

Item	Symbol	С	ondition	Min.	Тур.	Max.	Unit
Quiescent V _{CC} Supply Current	I _{QCCL}	V _{CC} = 15V, IN = 0V	V _{CC} - COM	-	-	26	mA
Fault Output Voltage	V_{FOH}	V _{SC} = 0V, V _{FO} Circui	t: 4.7kΩ to 5V Pull-up	4.5	-	-	V
	V_{FOL}	V _{SC} = 1V, V _{FO} Circui	t: 4.7kΩ to 5V Pull-up	-	-	0.8	V
Over Current Trip Level	V _{SC(ref)}	V _{CC} = 15V		0.45	0.5	0.55	V
Supply Circuit Under-	UV _{CCD}	Detection Level		10.7	11.9	13.0	V
Voltage Protection	UV _{CCR}	Reset Level		11.2	12.4	13.2	V
Fault-out Pulse Width	t _{FOD}	C _{FOD} = 33nF (Note 4)		1.4	1.8	2.0	ms
ON Threshold Voltage	V _{IN(ON)}	Applied between IN - COM		3.0	-	-	V
OFF Threshold Voltage	V _{IN(OFF)}	1		-	-	0.8	V
Resistance of Thermistor	R _{TH}	@ T _C = 25°C (Note F	ig. 9)	-	50	-	kΩ
		@ T _C = 80°C (Note F	ig. 9)	-	5.76	-	kΩ

Recommended Operating conditions

ltem	Symbol	Condition		Тур.	Max.	Unit
Input Supply Voltage	V _I	Applied between R - S		-	264	V_{rms}
Output Voltage	V_{PN}	Applied between P - N	-	280	400	V
Control Supply Voltage	V _{CC}	Applied between V _{CC} - COM	13.5	15	16.5	V
Control Supply Variation	dV _{CC} /dt	Applied between IN - COM		-	1	V/μs
PWM Input Signal	f _{PWM}	$T_C \le 100$ °C, $T_J \le 125$ °C, Per IGBT	-	20	-	kHz

Note
3. toN and toFF include the propagation delay time of the internal drive IC. tc(ON) and tc(OFF) are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Fig. 4

Note
4. The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation : $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[F]$

Electrical Characteristics

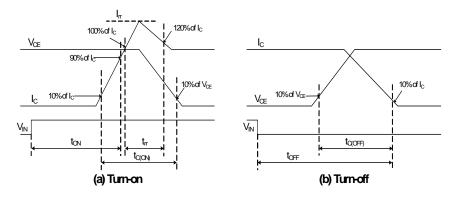


Fig. 4. Switching Time Definition

Mechanical Characteristics and Ratings

Item		Condition		Units		
item	'	Min.	Тур.	Max.	Units	
Mounting Torque	Mounting Screw: - M3	Recommended 0.62N•m	0.51	0.62	0.72	N•m
Device Flatness	Note Fig. 5		0	-	+120	μm
Weight			-	15.00	-	g

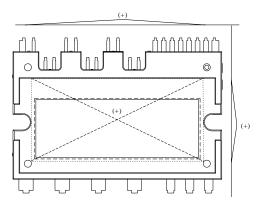
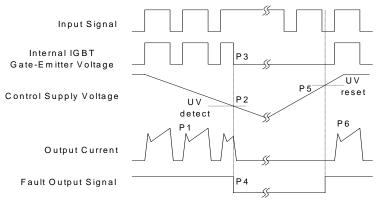


Fig. 5. Flatness Measurement Position

Time Charts of SPMs Protective Function

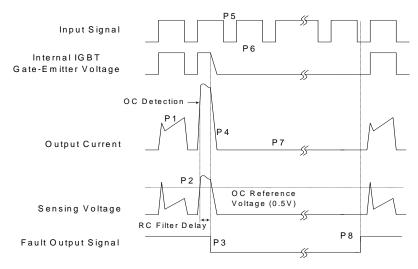


P1: Normal operation - IGBT ON and conducting current

P2 : Under voltage detection P3 : IGBT gate interrupt P4 : Fault signal generation P5 : Under voltage reset

P6: Normal operation - IGBT ON and conducting current

Fig. 6. Under-Voltage Protection



P1 : Normal operation - IGBT ON and conducting current

P2 : Over current detection

P3: IGBT gate interrupt / Fault signal generation

P4: IGBT is slowly turned off

P5 : IGBT OFF signal

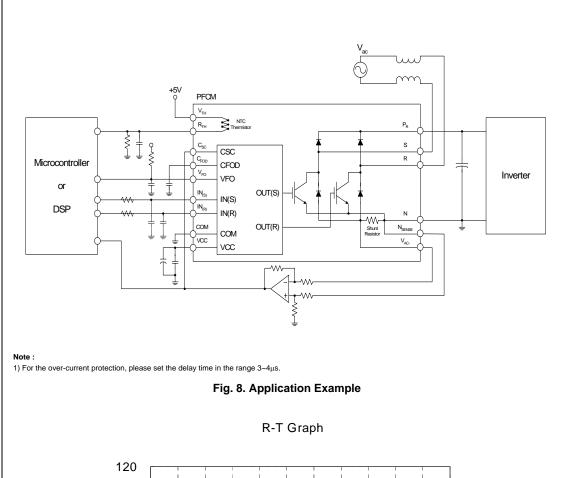
P6: IGBT ON signal - but IGBT cannot be turned on during the fault Output activation

P7: IGBT OFF state

P8 : Fault Output reset and normal operation start

Fig. 7. Over Current Protection

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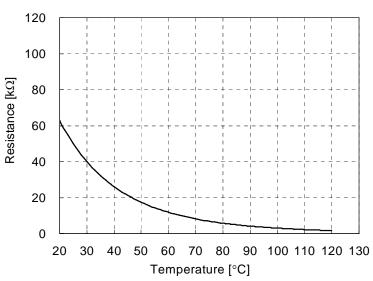
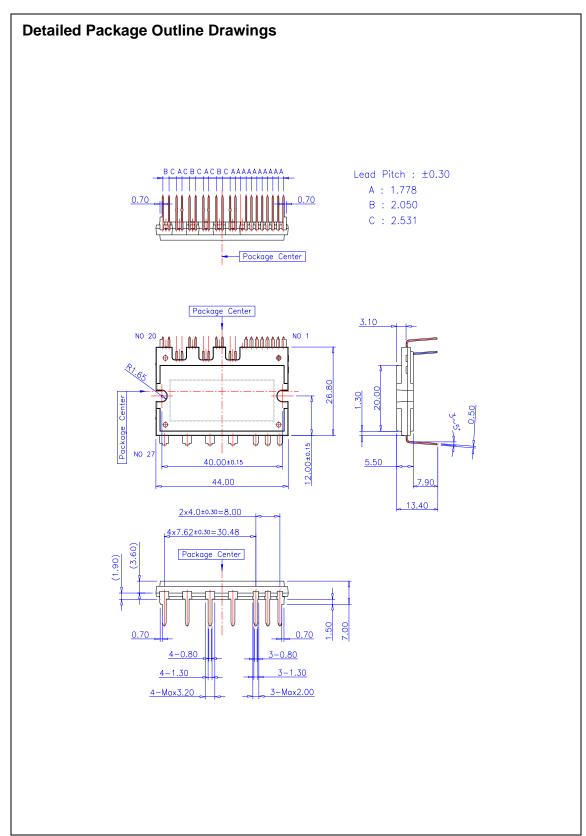
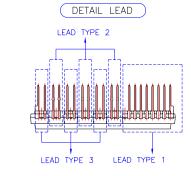


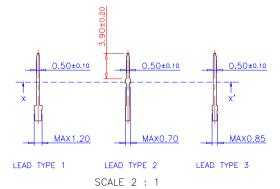
Fig. 9. R-T Curve of the Built-in Thermistor

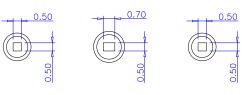


Detailed Package Outline Drawings 30.60 26.50 11.90±0.30 27.90±0.30 4.10±0.30 Lead Forming Dimension Package Center Package Center (2.76)(2.76)19.694±0.30 20.447±0.30 19.24±0.30 19.24±0.30 PKG Center to Lead Distance

Detailed Package Outline Drawings







LEAD TYPE 1 LEAD TYPE 2 LEAD TYPE 3

SCALE 5 : 1

LEAD SECTION X-X'

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